

[h3] Abstract of the Disclosure

[p31] The present invention describes a method of forming a thin film on a substrate arranged in a deposition system comprising the step of introducing a pre-determined amount of an impurity in a confined volume in the deposition system. One or more gases are introduced into the deposition system for forming the thin film. The impurity is removed from the confined volume in a gas phase during formation of the thin film. The impurity in the gas phase is incorporated into the thin film.